

To all our customers

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Renesas Technology Corp.  
Customer Support Dept.  
April 1, 2003

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Keep safety first in your circuit designs!

1. Renesas Technology Corporation puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage.

Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

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# 2SB831

Silicon PNP Epitaxial

**RENESAS**

ADE-208-1033 (Z)  
1st. Edition  
Mar. 2001

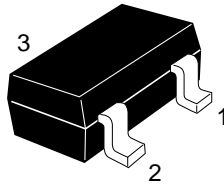
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## Application

- Low frequency amplifier
- Complementary pair with 2SD1101

## Outline

MPAK



1. Emitter
2. Base
3. Collector

# 2SB831

## Absolute Maximum Ratings (Ta = 25°C)

| Item                         | Symbol        | Ratings     | Unit |
|------------------------------|---------------|-------------|------|
| Collector to base voltage    | $V_{CBO}$     | -25         | V    |
| Collector to emitter voltage | $V_{CEO}$     | -20         | V    |
| Emitter to base voltage      | $V_{EBO}$     | -5          | V    |
| Collector current            | $I_C$         | -0.7        | A    |
| Collector peak current       | $i_{C(peak)}$ | -1          | A    |
| Collector power dissipation  | $P_C$         | 150         | mW   |
| Junction temperature         | $T_j$         | 150         | °C   |
| Storage temperature          | $T_{stg}$     | -55 to +150 | °C   |

## Electrical Characteristics (Ta = 25°C)

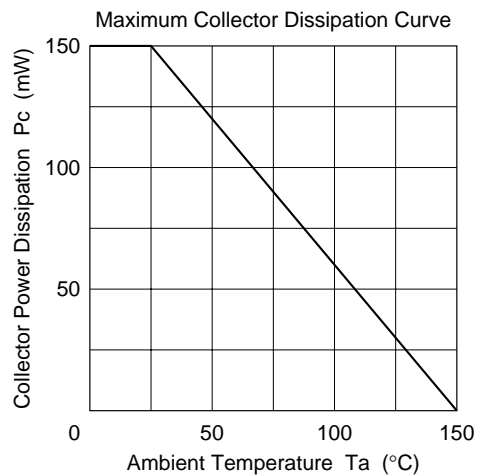
| Item                                    | Symbol        | Min | Typ | Max  | Unit    | Test conditions                                     |
|---|---------------|-----|-----|------|---------|---|
| Collector to base breakdown voltage     | $V_{(BR)CBO}$ | -25 | —   | —    | V       | $I_C = -10 \mu A, I_E = 0$                          |
| Collector to emitter breakdown voltage  | $V_{(BR)CEO}$ | -20 | —   | —    | V       | $I_C = -1 \text{ mA}, R_{BE} = \infty$              |
| Emitter to base breakdown voltage       | $V_{(BR)EBO}$ | -5  | —   | —    | V       | $I_E = -10 \mu A, I_C = 0$                          |
| Collector cutoff current                | $I_{CBO}$     | —   | —   | -1.0 | $\mu A$ | $V_{CB} = -20 \text{ V}, I_E = 0$                   |
| DC current transfer ratio               | $h_{FE}^{*1}$ | 85  | —   | 240  |         | $V_{CE} = -1 \text{ V}, I_C = -0.15 \text{ A}^{*2}$ |
| Collector to emitter saturation voltage | $V_{CE(sat)}$ | —   | —   | -0.5 | V       | $I_C = -0.5 \text{ A}, I_B = -0.05 \text{ A}^{*2}$  |
| Base to emitter voltage                 | $V_{BE}$      | —   | —   | -1.0 | V       | $V_{CE} = -1 \text{ V}, I_C = -0.15 \text{ A}^{*2}$ |

Notes: 1. The 2SB831 is grouped by  $h_{FE}$  as follows.

2. Pulse test

| Grade    | B         | C          |
|----------|-----------|------------|
| Mark     | BB        | BC         |
| $h_{FE}$ | 85 to 170 | 120 to 240 |

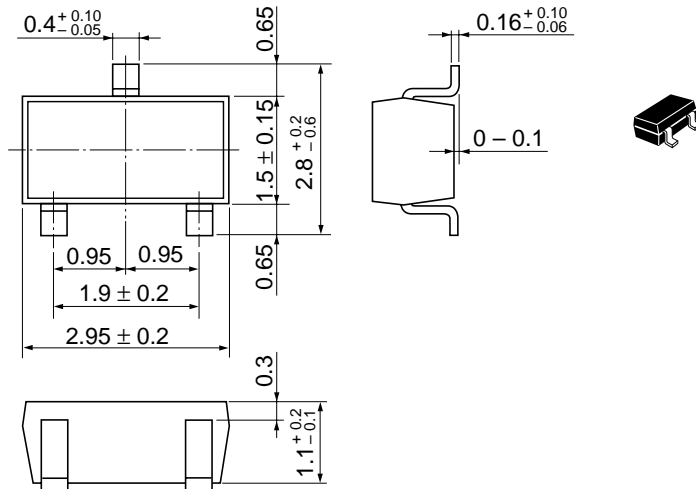
See characteristic curves of 2SB561.



Package Dimensions

As of January, 2001

Unit: mm



|                        |          |
|------------------------|----------|
| Hitachi Code           | MPAK     |
| JEDEC                  | —        |
| EIAJ                   | Conforms |
| Mass (reference value) | 0.011 g  |

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# HITACHI

## Hitachi, Ltd.

Semiconductor & Integrated Circuits.

Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL       NorthAmerica       : <http://semiconductor.hitachi.com/>  
           Europe                : <http://www.hitachi-eu.com/hel/ecg>  
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### For further information write to:

Hitachi Semiconductor  
(America) Inc.  
179 East Tasman Drive,  
San Jose, CA 95134  
Tel: <1> (408) 433-1990  
Fax: <1> (408) 433-0223

Hitachi Europe GmbH  
Electronic Components Group  
Dornacher Straße 3  
D-85622 Feldkirchen, Munich  
Germany  
Tel: <49> (89) 9 9180-0  
Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.  
Electronic Components Group.  
Whitebrook Park  
Lower Cookham Road  
Maidenhead  
Berkshire SL6 8YA, United Kingdom  
Tel: <44> (1628) 585000  
Fax: <44> (1628) 585160

Hitachi Asia Ltd.  
Hitachi Tower  
16 Collyer Quay #20-00,  
Singapore 049318  
Tel : <65>-538-6533/538-8577  
Fax : <65>-538-6933/538-3877  
URL : <http://www.hitachi.com.sg>

Hitachi Asia Ltd.  
(Taipei Branch Office)  
4/F, No. 167, Tun Hwa North Road,  
Hung-Kuo Building,  
Taipei (105), Taiwan  
Tel : <886>-(2)-2718-3666  
Fax : <886>-(2)-2718-8180  
Telex : 23222 HAS-TP  
URL : <http://www.hitachi.com.tw>

Hitachi Asia (Hong Kong) Ltd.  
Group III (Electronic Components)  
7/F., North Tower,  
World Finance Centre,  
Harbour City, Canton Road  
Tsim Sha Tsui, Kowloon,  
Hong Kong  
Tel : <852>-(2)-735-9218  
Fax : <852>-(2)-730-0281  
URL : <http://www.hitachi.com.hk>